75V N-CHANNEL ENHANCEMENT MODE MOSFET
PowerDI3333-8

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_A = +25°C
75V	22mΩ @ V_{GS} = 10V	7.8A
	28mΩ @ V_{GS} = 4.5V	6.9A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Backlighting
- Power Management Functions
- DC-DC Converters

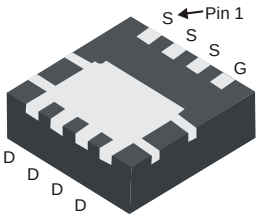
Features and Benefits

- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low $R_{DS(ON)}$ – Ensures On-state Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

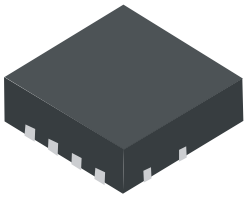
Mechanical Data

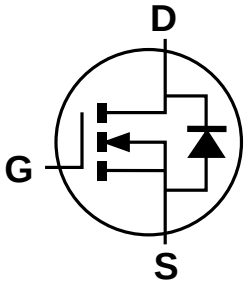
- Case: PowerDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.072 grams (Approximate)

PowerDI3333-8



Bottom View


Top View



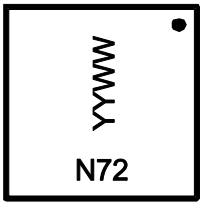
Equivalent Circuit

Ordering Information (Note 5)

Part Number	Case	Packaging
DMN7022LFGQ-7	PowerDI3333-8	2,000/Tape & Reel
DMN7022LFGQ-13	PowerDI3333-8	3,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



N72= Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 17 = 2017)
WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	75	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 7) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	7.8 6.2	A
Continuous Drain Current (Note 8) V_{GS} = 10V	Steady State	T_C = +25°C T_C = +70°C	I_D	23 18	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	56	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	2.1	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I_{SM}	50	A
Avalanche Current, L = 0.1mH (Note 9)			I_{AS}	28.8	A
Avalanche Energy, L = 0.1mH (Note 9)			E_{AS}	42.2	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)		P_D	0.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	125	°C/W
	t<10s		67	
Total Power Dissipation (Note 7)		P_D	2	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	$R_{\theta JA}$	62	°C/W
	t<10s		34	
Thermal Resistance, Junction to Case (Note 8)		$R_{\theta JC}$	6.9	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 10)						
Drain-Source Breakdown Voltage	BV_{DSS}	75	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current (T_J = +25°C)	I_{DSS}	—	—	1	µA	V_{DS} = 75V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 10)						
Gate Threshold Voltage	$V_{GS(TH)}$	1	—	3	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	14.6	22	mΩ	V_{GS} = 10V, I_D = 7.2A
		—	20.5	28		V_{GS} = 4.5V, I_D = 6.4A
Diode Forward Voltage	V_{SD}	—	0.72	—	V	V_{GS} = 0V, I_S = 3.2A
DYNAMIC CHARACTERISTICS (Note 11)						
Input Capacitance	C_{iss}	—	2737	—	pF	V_{DS} = 35V, V_{GS} = 0V, f = 1MHz
Output Capacitance	C_{oss}	—	126	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	96.1	—	pF	
Gate Resistance	R_g	—	0.89	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	26.4	—	nC	V_{DS} = 38V, I_D = 7.2A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	56.5	—	nC	
Gate-Source Charge	Q_{gs}	—	12	—	nC	
Gate-Drain Charge	Q_{gd}	—	11.8	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	6.1	—	ns	V_{GS} = 10V, V_{DS} = 38V, R_g = 1Ω, I_D = 5.7A
Turn-On Rise Time	t_R	—	5.7	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	19.6	—	ns	
Turn-Off Fall Time	t_F	—	3.9	—	ns	
Body Diode Reverse Recovery Time	t_{RR}	—	26.2	—	ns	I_F = 5.7A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	—	25.2	—	nC	

Notes:
6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
8. Thermal resistance from junction to soldering point (on the exposed drain pad).
9. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
10. Short duration pulse test used to minimize self-heating effect.
11. Guaranteed by design. Not subject to product testing.

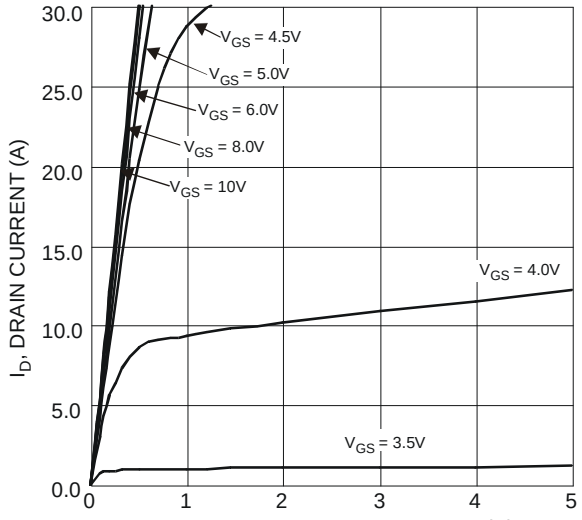


Figure 1 Typical Output Characteristics

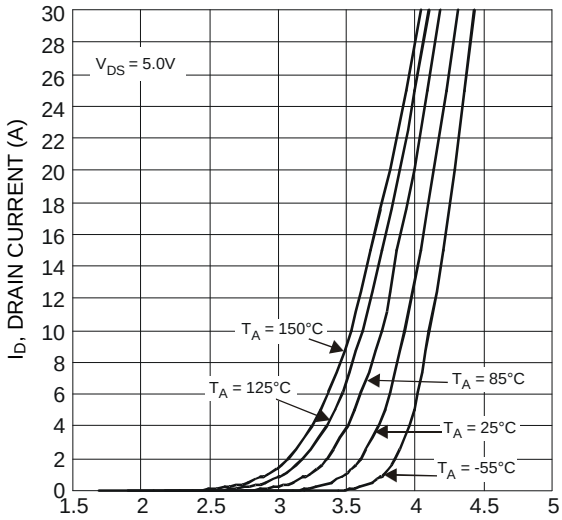


Figure 2 Typical Transfer Characteristics

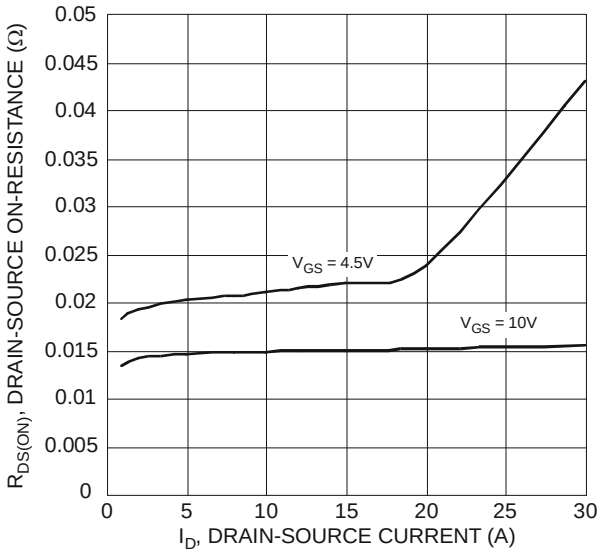


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

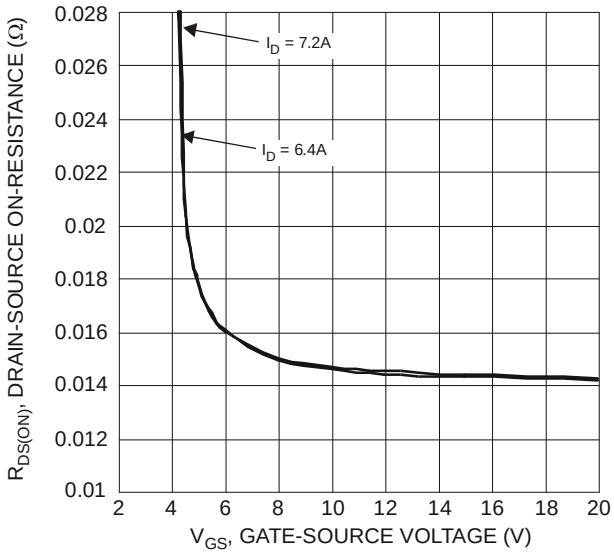


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

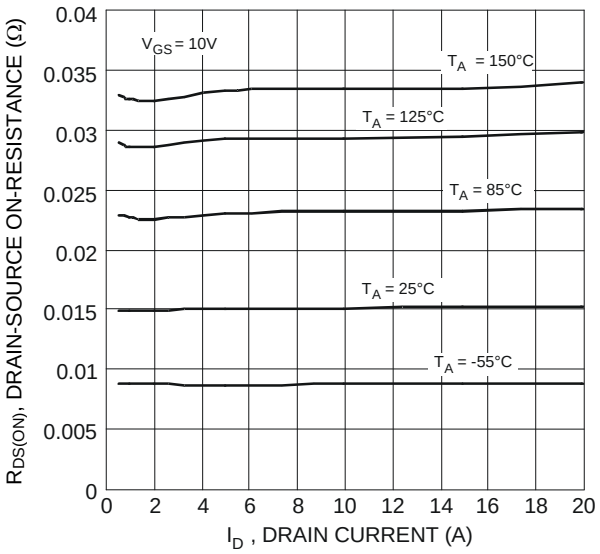


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

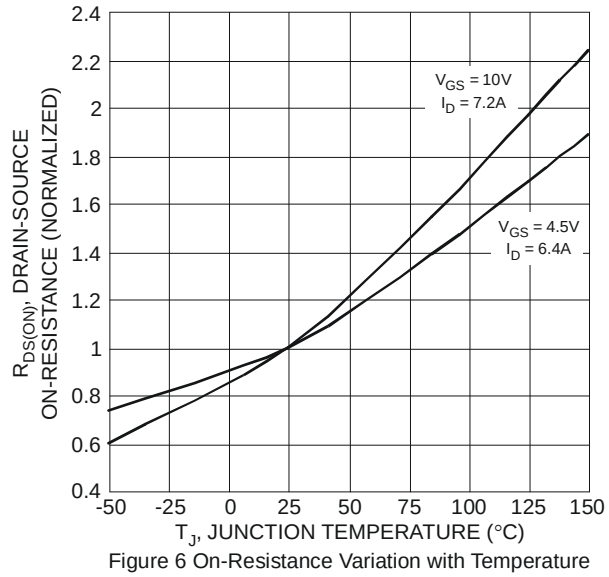


Figure 6 On-Resistance Variation with Temperature

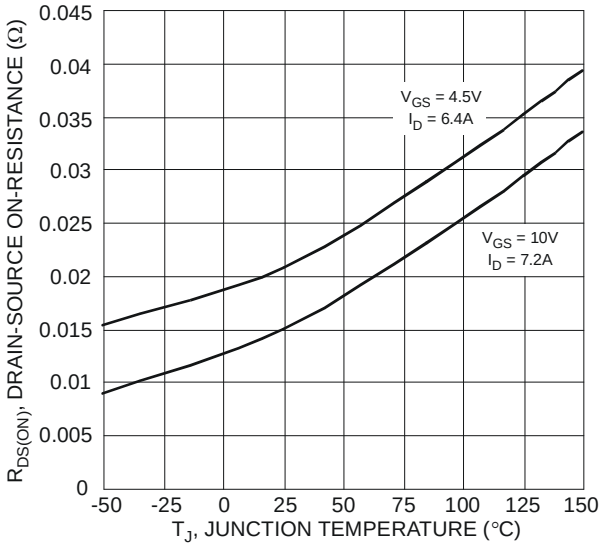


Figure 7 On-Resistance Variation with Temperature

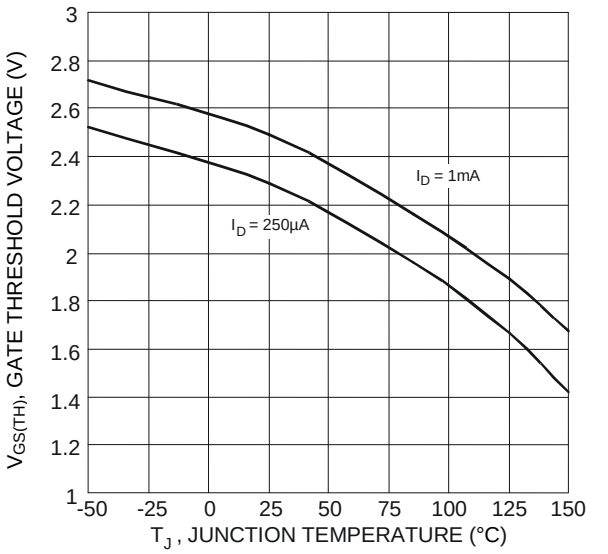


Figure 8 Gate Threshold Variation vs Junction Temperature

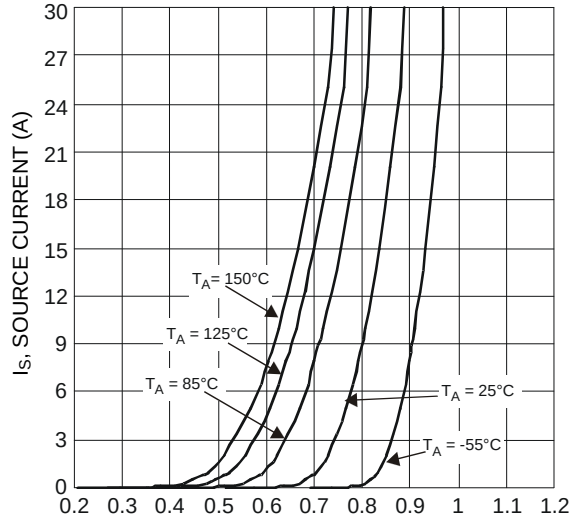


Figure 9 Diode Forward Voltage vs. Current

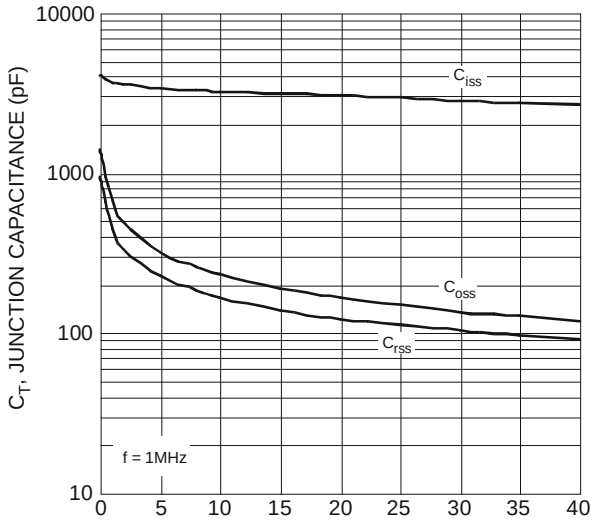


Figure 10 Typical Junction Capacitance

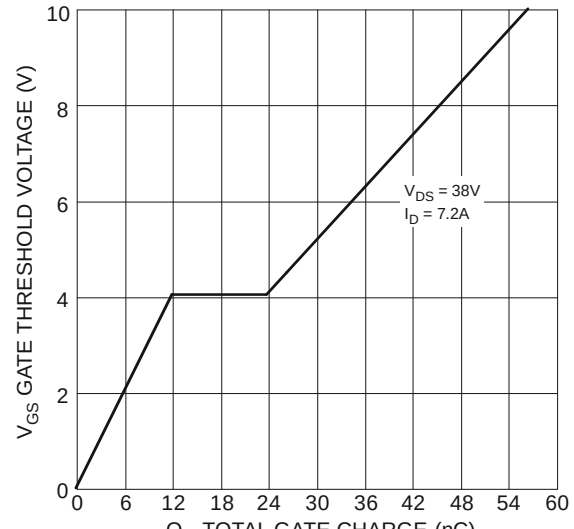


Figure 11 Gate Charge

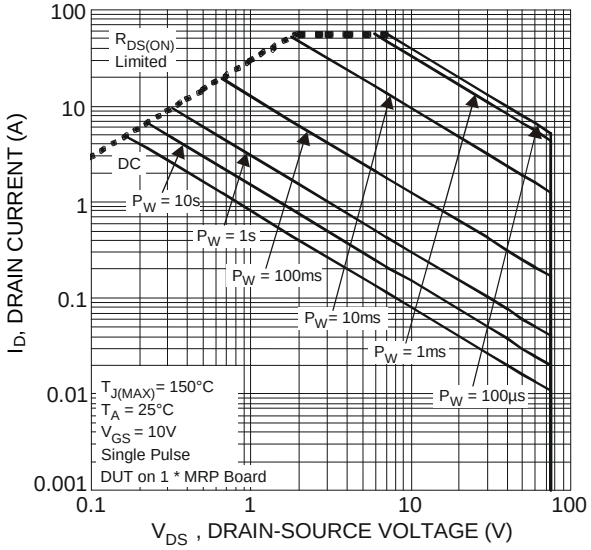


Figure 12 SOA, Safe Operation Area

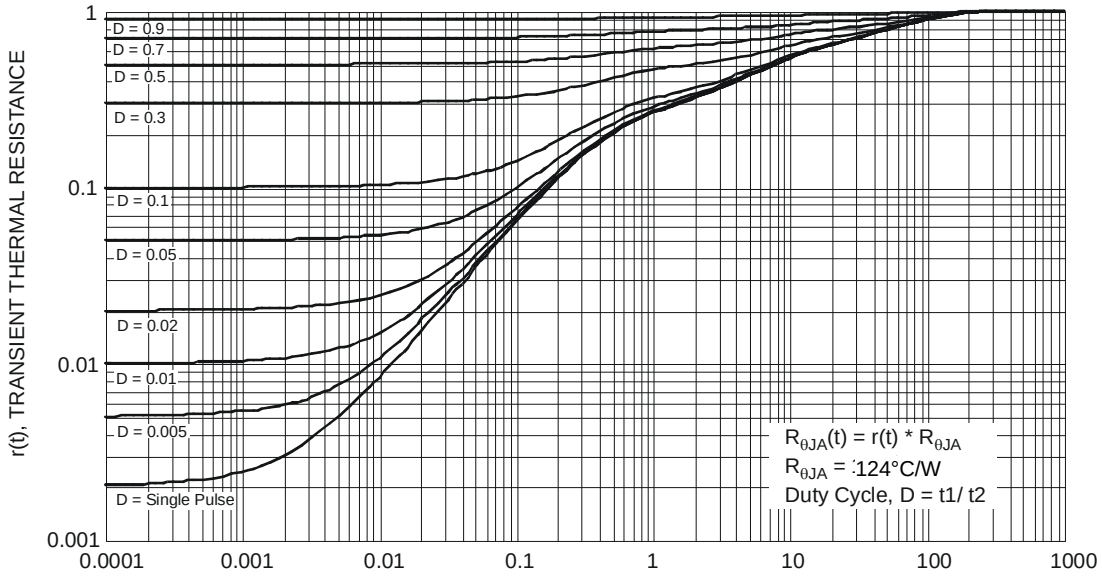
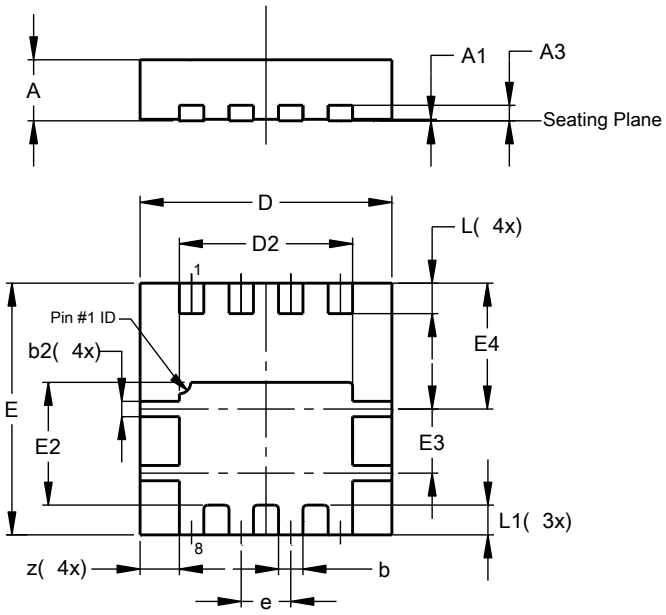


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

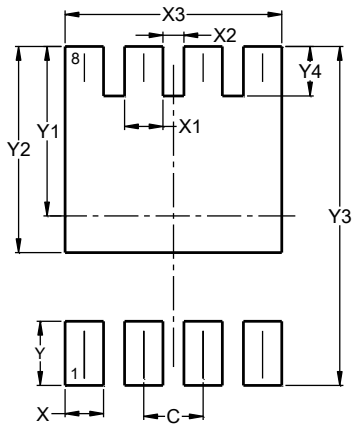


PowerDI3333-8			
Dim	**Min**	**Max**	**Typ**
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	–	–	0.203
b	0.27	0.37	0.32
b2	0.15	0.25	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
E4	1.60	1.70	1.65
e	–	–	0.65
L	0.35	0.45	0.40
L1	–	–	0.39
z	–	–	0.515
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540